

# **ORIENT**

# Photo coupler

# **Product Data Sheet**

Part Number:	OR-3H4
Customer:	
Date:	

## SHENZHEN ORIENT COMPONENTS CO.,LTD.

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#### 1. Features

- (1) Current transfer ratio(CTR): MIN. 20% at IF =  $\pm 1$ mA, VCE = 5V, Ta=25 °C
- (2) High input-output isolation voltage.(VISO=3,750Vrms)
- (3) BVCEO = 80V(MIN)
- (4) Operating temperature:-55°C to 125°C
- (5) ESD pass HBM 8000V/MM 2000V
- (6) Safety approval

UL approved(No.E323844)

VDE approved(No.40029733)

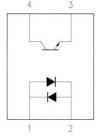
CQC approved (No.CQC19001231256)

- (7) In compliance with RoHS, REACH standards
- (8) MSL Class I

#### 2. Instructions

The OR-3H4 series device contains two infrared led and a photo transistor detector. They are encapsulated in a 4-pin SOP, free of halogens and Sb2O3





Anode, Cathode
 Emitter
 Cathode, Anode
 Collector

#### 3. Application Range

- (1) Hybrid substrates that require high density mounting
- (2) Programmable controller
- (3) System apparatus, measuring instruments

## 4. Max Absolute rated Value (Normal Temperature=25°C)

	Parameter	Symbol	Rated Value	Unit
Input	Forward Current	$I_{\mathrm{F}}$	50	mA
	Peak forward current(t=10us)	$I_{FM}$	1	A
	Reverse Voltage	$V_R$	6	V
	Power Dissipation	P	65	mW
	Junction Temperature	T <sub>j</sub>	125	°C
Output	Collector and emitter Voltage	$V_{CEO}$	80	V
	Emitter and collector Voltage	V <sub>ECO</sub>	7	
	Collector Current	$I_{C}$	50	mA
	Power Dissipation	P <sub>C</sub>	150	mW
	Junction Temperature	T <sub>j</sub>	125	°C
To	otal Power Dissipation	P <sub>tot</sub>	200	mW
*	*1 Insulation Voltage	V <sub>iso</sub>	3750	Vrms
O <sub>J</sub>	perating Temperature	$T_{\mathrm{opr}}$	-55 to +125	°C
S	storage Temperature	$T_{ m stg}$	-55 to +150	
*2 5	Soldering Temperature	T <sub>sol</sub>	260	



#### \*1. AC For 1 Minute, R.H. = $40 \sim 60\%$

Isolation voltage shall be measured using the following method.

- (1) Short between anode and cathode on the primary side and between collector and emitter on the secondary side.
- (2) The isolation voltage tester with zero-cross circuit shall be used.
- (3) The waveform of applied voltage shall be a sine wave.

## 5. Opto-electronic Characteristics(Normal Temperature=25°C)

Parameter		Symbol	Min	Тур.*	Max	Unit	Condition
T	Forward Voltage	$V_{\mathrm{F}}$		1.2	1.4	V	I <sub>F</sub> =±20mA
Input	Terminal Capacitance	$C_{t}$		60		pF	V=0, f=1KHz
	Collector Dark Current	$I_{CEO}$			100	nA	V <sub>CE</sub> =20V,I <sub>F</sub> =0mA
	Collector-Emitter Breakdown Voltage	$BV_{CEO}$	80			V	I <sub>C</sub> =0.1mA I <sub>F</sub> =0mA
Output	Emitter-Collector Breakdown Voltage	BV <sub>ECO</sub>	7			V	I <sub>E</sub> =0.1mA I <sub>F</sub> =0mA
	*1 Current Transfer Ratio	CTR	20		400	%	I <sub>F</sub> =±1mA V <sub>CE</sub> =5V
	Collector Current	$I_{\rm C}$	0.2		4	mA	
	Collector-Emitter Saturation Voltage	$V_{\text{CE(sat)}}$			0.4	V	$I_F=\pm 8mA$ $I_C=2.4mA$
	Insulation Impedance	$R_{iso}$	5×10 <sup>10</sup>	1×10 <sup>11</sup>		Ω	DC500V 40~60%R.H.
Transforming Characteristics	Floating Capacitance	$C_{\mathrm{f}}$		0.8	1	pF	V=0, f=1MHz
	Response Time	tr		3	18	μs	$ m V_{CE} = 10V$
	Descend Time	$t_{\mathrm{f}}$		4	18	μs	$I_{C}$ =2mA $R_{L}$ =100 $\Omega$

• Current Conversion Ratio =  $I_C / I_F \times 100\%$ 

<sup>\*2.</sup>soldering time is 10 seconds.



### 6. Rank table of current transfer ratio CTR

MODEL NO.	CTR Rank	Min.	Max.	Condition	Unit
	NO mark	20	400		
	A	50 250			
OR-3H4	В	100	400	IF=±1mA, V <sub>CE</sub> =5V, Ta=25°C	%
	С	100	200		
	CD 100 20	200	IF=±5mA, V <sub>CE</sub> =5V, Ta=25°C		
	GR	100	300	IF=±0.5mA, V <sub>CE</sub> =5V, Ta=25°C	

• Current Conversion Ratio =  $I_C / I_F \times 100\%$ 

## 7. Order Information

**Part Number** 

# OR-3H4W-X-Y-Z

Note

W = CTR Rank (A, B, C, GR or none)

X = Tape and reel option (TP or TP1).

Y = 'V' code for VDE safety (This options is not necessary).

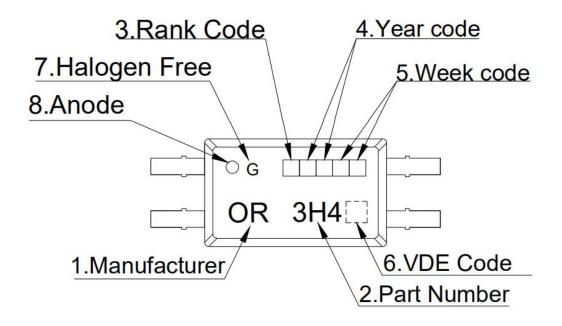
Z = G' code for Halogen free.

<sup>\*</sup> VDE Code can be selected.

Option	Description	Packing quantity
TP	Surface mount lead form (low profile) + TP tape & reel option	3000 units per reel
TP1	Surface mount lead form (low profile) + TP1 tape & reel option	3000 units per reel



## 8. Naming Rule



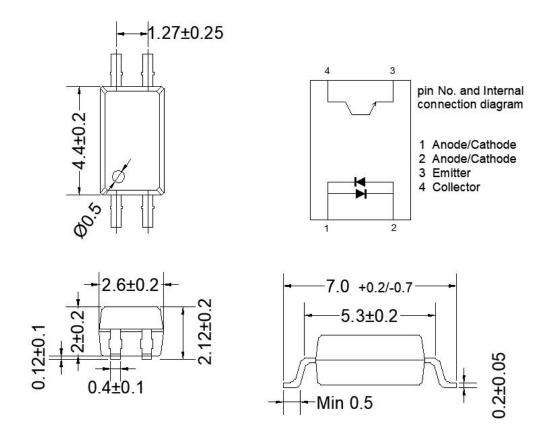
1. ]	Manufacturer :	: (	ORIENT.	
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- 2. Part Number: 3H4.
- 3. Rank Code : CTR Rank
- 4. Year Code : '0' means '2020' and so on.
- 5. Week Code : 01 means the first week, 02 means the second week and so on.
- 6. VDE Code [...]. (Optional)
- 7. HF Code 'G': Halogen Free.
- 8. Anode.

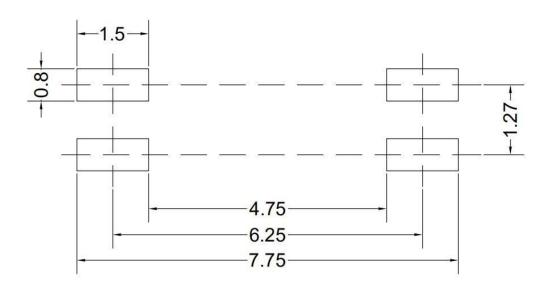
<sup>\*</sup> VDE Code can be selected.



## 9. Outer Dimension



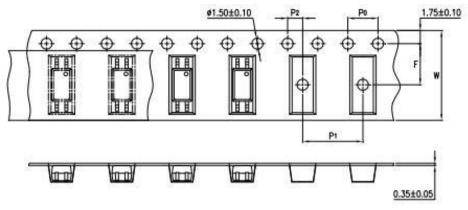
# 10. Recommended Foot Print Patterns (Mount Pad) (unit: mm)



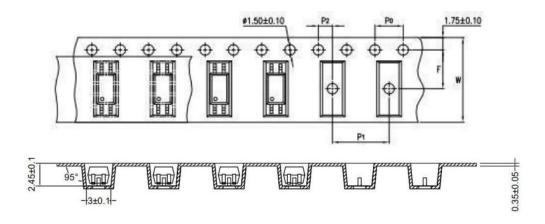


# 11. Taping Dimensions

# (1)OR-3H4-TP



# (2)OR-3H4-TP1



type	Symbol	Dimensions: mm (in.)
bandwidth	W	12±0.3 (0.47)
pitch	P0	4±0.1 (0.15)
pitch	F	5.5±0.1 (0.217)
	P2	2±0.1 (0.079)
interval	P1	8±0.1 (0.315)

Encapsulation type	TP/TP1
Quantity (pieces)	3000



# 12. Package Dimension

## (1) package dimension

Packing Information				
Packing type	Reel type			
Tape Width	12mm			
Qty per Reel	3,000pcs			
Small box (inner) Dimension	345*345*45mm			
Large box (Outer) Dimension	480x360x360mm			
Max qty per small box	6,000pcs			
Max qty per large box	60,000pcs			

#### (2)Packing Label Sample



#### Note:

- 1. Material Code :Product ID.
- 2. P/N :Contents with "Order Information" in the specification.
- 3. Lot No. :Product data.
- 4. D/C :Product weeks.
- 5. Quantity: Packaging quantity.



# 13. Reliability Test

NO.	Reliability			Reliability Testin	ng	
NO.	TTENIS	QTY. (Pcs)	Condition	Process	Device	Standard
1	RSH 耐焊接热	22	260±5℃	10s/3 次	锡炉	JESD22-A106
				168 hrs		
2	HTSL 高温存储	77	125℃	500 hrs		JESD22-A103
				1000 hrs		
				168 hrs	les VII bits	
3	LTSL 低温存储	77	-55℃	500 hrs	低温箱 测试仪	JESD22-A119
				1000 hrs		
4	TC 温度循环	77	H:125°C 15min  ∫ 5min  L:-55°C 15min	300 cycle	冷热冲击机	JESD22-A104
5	TS 温度冲击	77	H:100°C 5min  ∫ 15s L:-40°C 5min	300 cycle	冷热冲击机	JESD22-A106
			2. 10 0 011111	168 hrs		
6	HTOL	77	110°C IF=10mA	500 hrs		JESD22-A108
	高温操作		Vce=5V	1000 hrs	化电路板	322 <b>22</b> 1123
7	ESD-HBM 人体模式	22	≥8KV 1Cycle	1次	ESD静电测 试仪	JESD22-A114
8	SD 可焊性	22	Pb-free 245±5℃	5S/1次	锡炉	JESD22-B102
			HTRB	168 hrs		
9	HTRB 高温反向偏压	77	@125°C	500 hrs	高温烤箱 ,测试仪	JESD22-A103
		Vce=80v	1000 hrs	, MINI		
	HATED			168 hrs		
10	H3TRB 1() <b>温湿度反向偏</b>	H3TRB 且湿度反向偏 医,寿命试验  77  H3TRB 85°C,85%RH Vce=80v		500 hrs		JESD22-A101
	比,寿命试验   		Vce=80v	1000 hrs	—————————————————————————————————————	
11	Autoclave 压力锅	77	Ta=121 ℃,100%RH,2atm	96hrs	压力锅	JESD22-A102

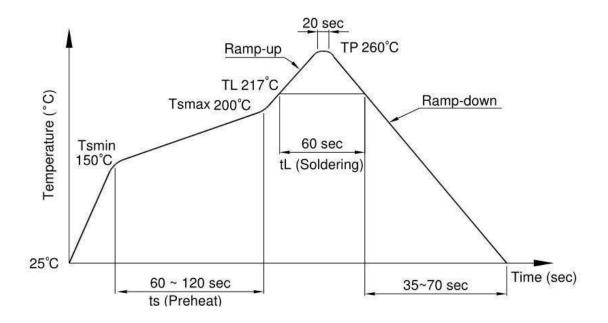


# 14. Temperature Profile Of Soldering

#### (1) IR Reflow soldering (JEDEC-STD-020C compliant)

One time soldering reflow is recommended within the condition of temperature and time profile shown below. Do not solder more than three times.

Profile item	Conditions
Preheat	
- Temperature Min (T Smin )	150°C
- Temperature Max (T Smax )	200°C
- Time (min to max) (ts)	90±30 sec
Soldering zone	
- Temperature (TL)	217°C
- Time (t L )	60 sec
Peak Temperature	260°C
Peak Temperature time	20 sec
Ramp-up rate	3°C / sec max.
Ramp-down rate from peak temperature	3~6°C / sec
Reflow times	≤3

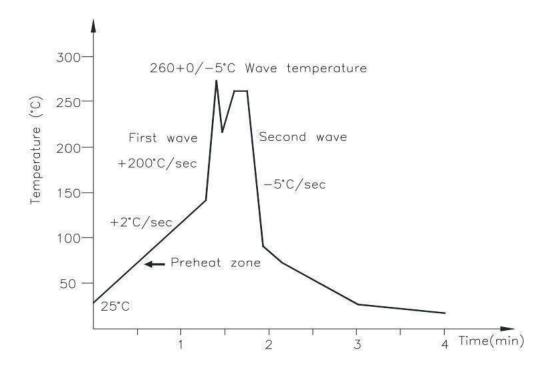




## (2) Wave soldering (JEDEC22A111 compliant)

One time soldering is recommended within the condition of temperature.

Temperature	260+0/-5°C
Time	10 sec
Preheat temperature	25 to 140°C
Preheat time	30 to 80 sec



## (3) Hand soldering by soldering iron

Allow single lead soldering in every single process. One time soldering is recommended.

Temperature	380+0/-5°C
Time	3 sec max



#### 1 · Characteristics Curve

Figure 1. Collector Power Dissipation vs. Ambient Temperature

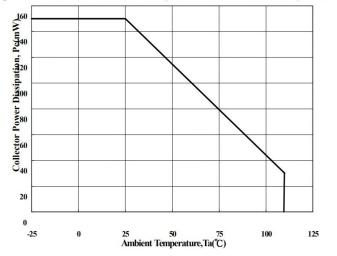


Figure 3. Forward Current vs. Forward Voltage

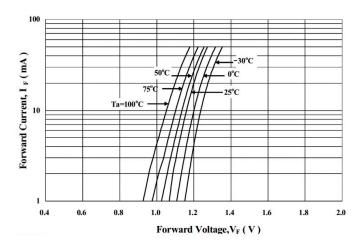


Figure 5. Pulse Forward Current vs. Duty Cycle Ratio

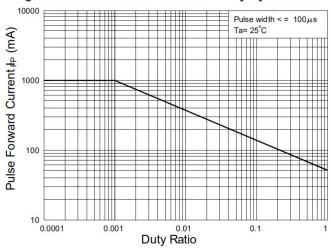


Figure 2. Forward Current vs. Ambient Temperature

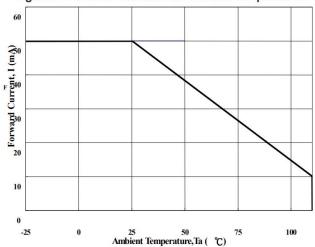


Figure 4. Forward Voltage Temperature Coefficient vs.

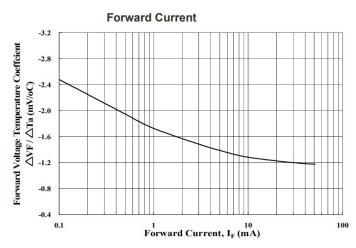


Figure 6. Pulse Forward Current vs. Pulse Forward

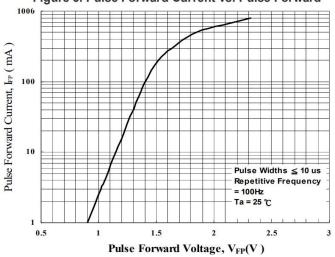




Figure 7. Collector-Emitter Saturation Voltage vs. Forward

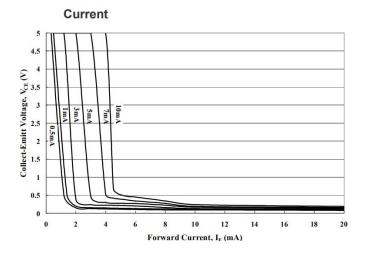


Figure 9. Collector Current vs. Small Collector-Emitter

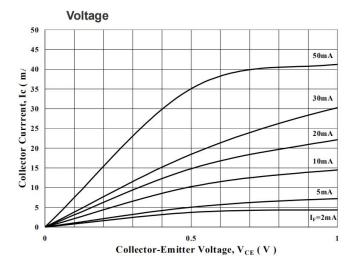


Figure 11. Collector Dark Current vs. Ambient Temperature

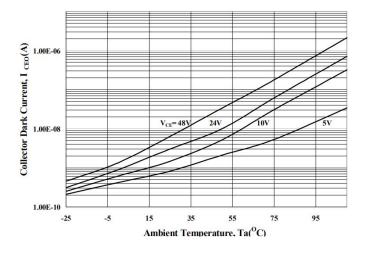


Figure 8. Collector Current vs. Collector-Emitter

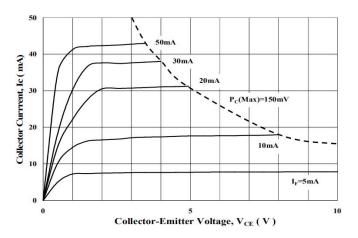


Figure 10. Normalized CTR vs. Forward Current

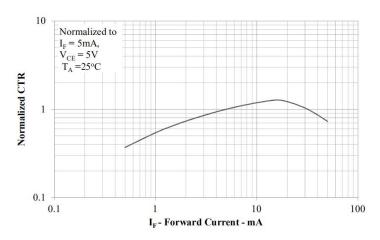


Figure 12. Current Transfer Ratio vs. Forward

Current

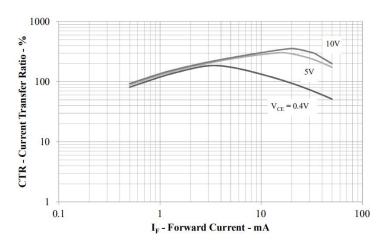




Figure 13. Normalized CTR vs. Ambient Temperature

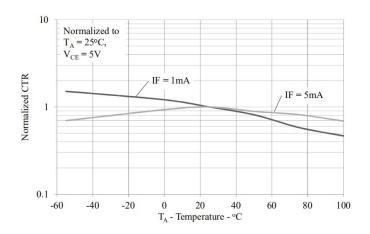


Figure 15. Collector Current vs. Ambient Temperature

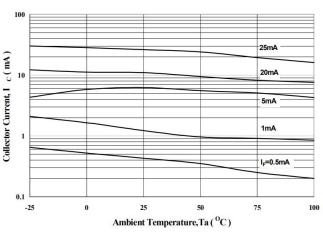
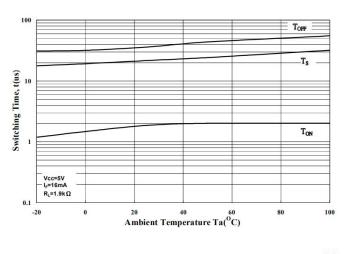


Figure 17. Switching Time vs. Ambient Temperature



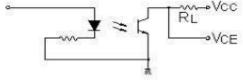


Figure 14. Collector-Emitter Saturation Voltage vs.

Ambient Temperature

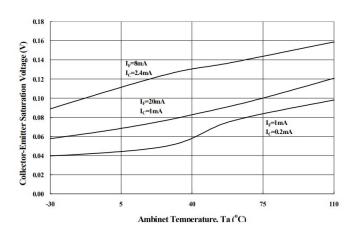


Figure 16. Switching Time vs. Load Resistance

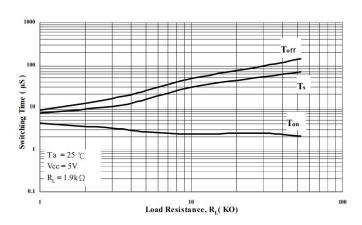


Figure 18. Frequency Response

